

**Please amend the claims as follows:**

1. (twice amended) A thin film transistor, comprising:  
a stepped substrate provided with a sidewall between upper and lower [portion] thereof;  
an active layer formed on the stepped substrate;  
a gate insulation film formed on a lower portion and a sidewall of the active layer contiguous the [lower portion] and sidewall of the stepped substrate, respectively;  
an insulating film formed on a lower portion and a sidewall of the gate [insulating film] contiguous the [lower portion] and sidewall of the stepped substrate, respectively;  
a gate electrode formed on the gate insulation film corresponding to the sidewalls of the substrate and the insulation film; and  
impurity regions in the active layer corresponding to the upper and lower portions of the substrate.

**REMARKS**

Claims 1, 2, and 4 to 6 remain in this application.

Claims 1 to 6 stand rejected under 35 U.S.C. 112, first paragraph, as lacking support for a single Z-shaped substrate. Consequently, this language has been deleted from claim 1. In addition, claim 3 has been canceled.